FIBER SENSORS

LASER SENSORS

PHOTOELECTRIC SENSORS

MICRO PHOTOELECTRIC SENSORS AREA SENSORS SAFETY LIGHT CURTAINS / SAFETY COMPONENTS PRESSURE / FLOW SENSORS INDUCTIVE PROXIMITY SENSORS PARTICULAR

SENSOR SIMPLE WIRE-SAVING UNITS WIRE-SAVING SYSTEMS MEASUREMENT SENSORS

> STATIC CONTROL DEVICES

LASER MARKERS

HUMAN MACHINE INTERFACES

FA COMPONENTS

MACHINE VISION SYSTEMS

UV CURING SYSTEMS

PLC

ENERGY MANAGEMENT

Wafer Mapping Sensor

Related Information

General terms and conditions...... F-3 General precautions P.1552~

Selection guide P.865~



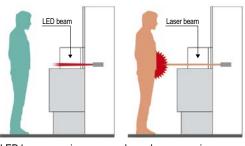




The safe LED beam reflective type wafer mapping sensor

Safe LEDs adopted

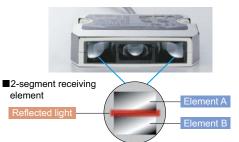
Conventional laser mapping sensor that adopts laser beam has been dangerous because an operator is exposed directly to laser beam, which comes out of the load port through FOUP. We have succeeded in developing LED to adopt as light source for M-DW1. Therefore an operator's safety is ensured.



LED beam mapping sensor Laser beam mapping sensor

Precise position detection by 2-segment receiving element

Wafer detection by the amount of reflected light may sometimes fail depending on the wafer edge shape. The M-DW1 uses 2-segment receiving element in the beam-receiving part, and detects wafers by the reflected light position instead of the amount of reflected light. Thus, the sensor is less affected by wafer thickness or the amount of reflected light.



Sensing of nitride-coated wafers possible

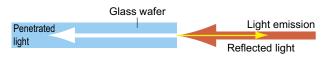
Nitride-coated wafers absorb light at certain wavelengths depending on the coating thickness. If the sensor uses the laser beam having a single wavelength, the beam may be absorbed completely, resulting in wafer detection error. The M-DW1 uses a LED light source with a wide wavelength band that allows to detect nitride-coated wafers successfully.

High-speed response time: 0.5 ms

The sensor responds in 0.5 ms, meeting the requirements of both high speed and high accuracy in wafer detection.

Glass wafers are also detectable

The M-DW1, which detects wafers not by the light amount but by the light position, can detect the glass wafers regardless of the light amount.



Compact and lightweight design with built-in amplifier

The sensor measures W80.6 mm × H18.3 mm × D50 mm W3.173 in × H0.720 in × D1.969 in, and weights only 75 g approx.





M-DW1 HD-T1

FIBER

ORDER GUIDE

<u> </u>								
Appearance			Center sensing distance	Sensing object	Model No.	Output		
		45 mm 1.772 in	45 mm 1.772 in	3 inch or larger semiconductor wafer	M-DW1	NPN output / PNP output selectable by switch		
1	SPECIFICATION	NS						
		r		L ED bear	n reflective type			
"har	Type m Model No.							
		l			M-DW1			
	marking directive compliance	<u> </u>			ive, RoHS Directive			
	nter sensing distance	t			nm 1.772 in niconductor wafer (Note	- ^\		
	ising object ectable surface	t	Surface ha	3 inch or larger sem		,		
_		L			ts light in the light receit ± 5° (Note 4)			
	ising angle fer pitch	L	Separate ser	12.5 ± Ising is possible at normal ser		in sitch or more (Note 5)		
	able cassette	t	<u>Ocparate cont</u>		JP cassette / open casse			
	pply voltage	1			% Ripple P-P 10 % or le			
	rent consumption	1			mA or less			
<u></u>	ent consumption	l						
		NPN output /		ctable with output selection sv	witch <pnp output=""></pnp>			
Out		NPN open-o	-collector transistor		PNP open-collec			
Outp	Jut	Applied		or less (between output and 0 V	 Applied volta 	source current: 100 mA age: 30 V DC or less (between output and +V)		
		Residu		ss (at 100 mA sink current) less (at 16 mA sink current)	Residual vol	Itage: 1 V or less (at 100 mA source current) 0.4 V or less (at 16 mA source current)		
	Utilization category	t		, , , , , , , , , , , , , , , , , , ,	12 or DC-13			
	Output operation	L			12 or DC-13 DN, selectable by switch			
	Short-circuit protection	t			estored automatically)	<u> </u>		
Res	sponse time	1) µs or less			
	eration indicator	l			up when the output is C			
· ·	bility indicator	1	Green LE	D (lights up under stable light	· · ·	,		
	er function	/		x. 2 ms fixed OFF-delay timer		,		
	t input (emission halt input)			Signal condition • Emission Halt: Open,				
Sen	sitivity selection input		Signal condition • Input OFF: Open, or 4 to 8 V • Input ON: 0 to 3 V, or 9 V to +V (26.4 V max.)					
Sen	sitivity setting			ng: effectuated with sensor's selection: 4 levels with sensor		n rels with external input selectable		
	Pollution degree	1		3 (Industr	rial environment)			
ce	Protection	I		IP	20 (IEC)			
Environmental resistance	Ambient temperature	I	0 to +55 °C +?	32 to +131 °F (No dew conde	ensation), Storage: -10	to +70 °C +14 to +158 °F		
resig	Ambient humidity	1		35 to 85 % RH, ξ	Storage: 35 to 85 % RH	I		
untal	Ambient illuminance	Incandesc	cent light: 3,000 {x c	or less at the light-receiving fr	ace, Fluorescent light: 1	1,500 {x or less at the light-receiving face		
nme	Voltage withstandability	1	1,000 V AC f	for one min. between all supp	ply terminals connected	together and enclosure		
iviro ⁶	Insulation resistance	21	$20 \text{ M}\Omega$, or more, with	n 250 V DC megger between	all supply terminals co	onnected together and enclosure		
Ē	Vibration resistance	1	10 to 500 Hz frequ	ency, 3 mm 0.118 in double	amplitude in X, Y and Z	Z directions for two hours each		
	Shock resistance	98 m/s ² acceleration (10 G approx) in X, Y and Z directions five times each						
Emi	tting element	1		LED ((modulated)			
Material		1	Enclosure: ABS and Stainless steel (SUS301), Lens: Acrylic					
-	le	1	0.15 mm ² 5-core cabtyre cable, 300 mm 11.811 in long					
Cabl		Extension up to total 10 m 32.808 ft is possible with 0.15 mm ² , or more, cable.						
	ole extension	۱ <u> </u>	Extensi	on up to total 10 m 32.808 ft	is possible with 0.15 m			

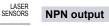
2) In case of 8 inch or less wafers, the wafer pitch, the orientation flat or surface condition may affect the sensing.

3) Polished wafers, etc., which have a sharp edge cannot be detected since they do not reflect the light in the light receiving direction.

4) Since the position of the orientation flat may vary by ±20° due to its rotation, refer to "Detecting wafer having orientation flat" (p.918) for detection of a wafer having an orientation flat.

5) This is the pitch of an 8 inch wafer near its center region when it is inserted in an inclined fashion. When detecting a wafer having an orientation flat, the wafer pitch becomes still smaller when sensing at positions which avoid the orientation flat. In this case, the sensing signal cannot be resolved and it becomes a continuous, broad signal. For details, refer to "Sensing signal" (p.919~).

I/O CIRCUIT DIAGRAMS



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SIMPLE WIRE-SAVING UNITS

WIRE-SAVING SYSTEMS

MEASURE-MENT SENSORS

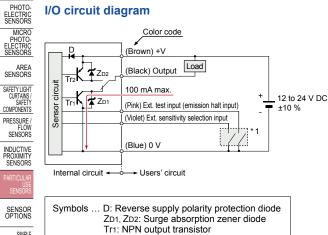
STATIC CONTROL DEVICES

LASER MARKERS

PLC

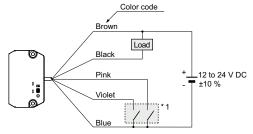
HUMAN

I/O circuit diagram



Tr2: PNP output transistor

Wiring diagram



* 1

Non-voltage contact or NPN open-collector transistor

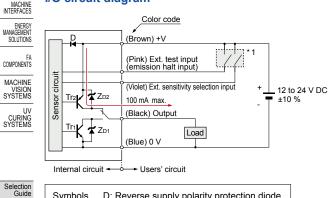
External test input (emission halt input)
 0 to 3 V, or 9 V to +V (26.4 V max.): Emission halt

or

- Open, or 4 to 8 V: Emission
- External sensitivity selection input 0 to 3 V, or 9 V to +V (26.4 V max.): Input ON Open, or 4 to 8 V: Input OFF

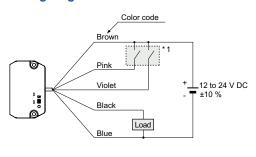
PNP output

I/O circuit diagram



ymbols	D: Reverse supply polarity protection diode
	ZD1, ZD2: Surge absorption zener diode
	Tr1: NPN output transistor
	Tr2: PNP output transistor

Wiring diagram



* 1

Non-voltage contact or PNP open-collector transistor or · External test input (emission halt input) 0 to 3 V, or 9 V to +V (26.4 V max.): Emission halt

- Open, or 4 to 8 V: Emission External sensitivity selection input 0 to 3 V, or 9 V to +V (26.4 V max.): Input ON Open, or 4 to 8 V: Input OFF

Liquid Leak Detection Liquid Level Detection

Water Detection

S

HD-T1

PRECAUTIONS FOR PROPER USE

- · Never use this product as a sensing device for personnel protection. · In case of using sensing devices for
- personnel protection, use products which meet laws and standards, such as OSHA, ANSI or IEC etc., for personnel protection applicable in each region or country.

Mounting

· Set the distance between the sensor detection surface and the wafer edge to be 45 mm 1.772 in and mount the sensor so that sensing is done at an angle of 12.5° with respect to the wafer. Mount using M4 (length 16 mm 0.630 in) screws. The tightening torque should be 1.2 N·m or less. Further, although the sensing distance may change due to variation in the wafer position (wafer protrusion, orientation flat position, etc.), if it is within 5 mm 0.197 in, stable sensing is possible.



Mounting angle 12.5° -Sensor axis -Wafer center axis Spot position

Note: If the wafer center axis and the sensor axis lie along a straight line (0°), detection is not possible. Always mount the sensor at an angle to the wafer.

Wiring

Top-view

- · Make sure that the power supply is off while wiring.
- · Take care that wrong wiring will damage the product.
- · Verify that the supply voltage variation is within the rating.
- · If power is supplied from a commercial switching regulator, ensure that the frame ground (F.G.) terminal of the power supply is connected to an actual ground.
- · In case noise generating equipment (switching regulator, inverter motor, etc.) is used in the vicinity of this product, connect the frame ground (F.G.) terminal of the equipment to an actual ground.
- Extension up to total 10 m 32.808 ft, or less, is possible with 0.15 mm², or more, cable. However, in order to reduce noise, make the wiring as short as possible.
- · Do not run the wires together with high-voltage lines or power lines or put them in the same raceway. This can cause malfunction due to induction.
- · Make sure to use an isolation transformer for the DC power supply. If an autotransformer (single winding transformer) is used, this product or the power supply may get damaged.
- In case a surge is generated in the used power supply, connect a surge absorber to the supply and absorb the surge.

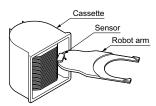
Others

- Do not use during the initial transient time (0.5 sec.) after the power supply is switched on.
- · Take care that the sensor is not directly exposed to fluorescent lamp from a rapid-starter lamp, a high frequency lighting device or sunlight etc., as it may affect the sensing performance.
- · Avoid dust, dirt, and steam.
- Take care that the product does not come in contact with water, oil, grease or organic solvents, such as, thinner, etc.
- · Do not allow any water, oil, fingerprints, etc., which may refract light, or dust, dirt, etc., which may block light, to stick to the sensing surfaces of the sensor. In case they are present, wipe them with a clean, dust-free soft cloth or lens paper.

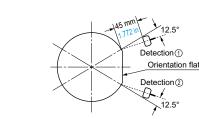
Refer to p.1552~ for general precautions.

Detecting wafer having orientation flat

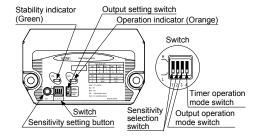
· When detecting a wafer having an orientation flat, mount the sensor so that a portion other than the orientation flat is detected. Further, arrange to detect the wafer from two different angles by moving the robot arm, etc., and OR the signal so obtained.







Part description



Sensitivity selection setting

· Sensitivity can be selected from four levels by appropriate setting of the sensitivity selection switch (2 bits).



Liquid Level Detection
Water Detection
Color Mark Detection
Wafer Detection
Ultrasonic
Small / Slim Object Detection
Obstacle Detection
M-DW1
HD-T1

Notes: 1) In case of 8 inch or less wafers, the wafer pitch, orientation flat or the surface condition may affect the sensing.

2) Polished wafers, etc., which have a sharp edge cannot be detected since they do not reflect the light in the light receiving direction.

LASER SENSORS PHOTO-ELECTRIC SENSORS MICRO PHOTO-ELECTRIC SENSORS

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PRESSURE / FLOW SENSORS INDUCTIVE PROXIMITY SENSORS

SENSOR OPTIONS SIMPLE WIRE-SAVING UNITS

WIRE-SAVING SYSTEMS

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Selection Guide

PRECAUTIONS FOR PROPER USE

External sensitivity selection input

 The external sensitivity selection input (violet) becomes ON when it is connected to 0 to 3 V, or 9 V to +V (26.4 V max.), and becomes OFF when it is kept open or connected to 4 to 8 V.

If the sensitivity is selected with the external sensitivity selection input, set the sensitivity selection switch as shown in the table below.

Sensitivity selection switch	Ext. sensitivity sele	Sensitivity	
	0 to 3 V, or 9 V to +V (26.4 V max.)	ON	Maximum sensitivity (MAX)
	Open, or 4 to 8 V	OFF	Medium sensitivity (MID)
	0 to 3 V or 9 V to +V (26.4 V max.)	ON	High sensitivity (HIGH)
	Open, or 4 to 8 V	OFF	Low sensitivity (LOW)

Note: For details of sensitivity, refer to "Sensitivity selection setting" (p.918).

Sensitivity setting

- Although this sensor has an optical system which makes it difficult for the background to affect the detection, the background may have an effect when detecting small diameter wafers. Hence, if the background gets detected, or the stability indicator (green) lights off when the cassette has no wafers, sensitivity setting should be done so that the background does not have an effect. However, the sensitivity reduces when sensitivity setting is done.
 - Since the sensitivity is stored in an EEPROM when the sensitivity setting button is pressed, the setting need not be repeated when the power is switched on again. However, note that the EEPROM has a lifetime and its guaranteed life is 100,000 write operation cycles.

Light emission control function

 Light emission is halted when the external light emission control input (pink) is connected to 0 to 3 V, or 9 V to +V (26.4 V max.). In this case, the output turns to the dark state.

Time chart

Selection Guide

Liquid Leak Detection

Liquid Level Detection

Water Detection

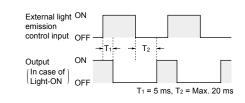
Color Mark Detection

Ultrasonic

Small / Slim Object Detection

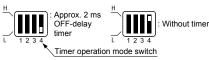
Obstacle Detection

HD-T1

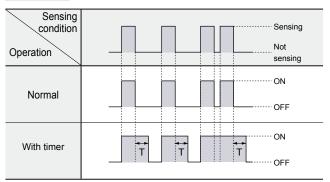


Timer function

• Using the timer operation mode switch, it is possible to select an approx. 2 ms fixed OFF-delay timer. Since the output is extended by a fixed period, it is useful when the connected device has a slow response time.



Time chart



Timer period: T = Approx. 2 ms

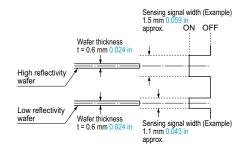
Sensing signal

Sensing signal width

- The sensing signal which is output from the sensor is as follows: The sensing signal has a width larger than the thickness of the wafer.
- (2) The signal width also varies with the reflectivity of the sensing edge. High reflectivity (polish, aluminum evaporated, etc.): Large signal width
 Example: Wafer thickness t = 0.6 mm 0.024 in
 Signal width
 1.5 mm 0.059 in approx.

Low reflectivity (nitride or oxide film processed): Small signal width Example: Wafer thickness t = 0.6 mm 0.024 in Signal width 1.1 mm 0.043 in approx.

③The signal width also changes with the sensing distance or the sensing angle.

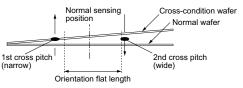


 From the above, for determining the position of the wafer from the sensing signal, calculate the center position of the signal's ON region, while taking into consideration the response time.

PRECAUTIONS FOR PROPER USE

Narrow pitch sensing signal width

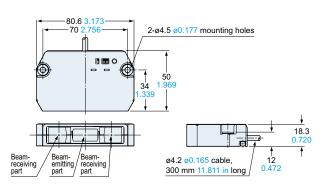
• In case of "Detecting wafer having orientation flat" (p.918), when the sensor is mounted at positions which avoid the wafer orientation flat, the pitch of a crosscondition wafer changes as shown in the figure below.



• The calculated pitch based on the wafer size is given in the table below.

Wafer size	Normal pitch	Orientation flat length	Wafer thickness	Cross pitch (narrow)	Cross pitch (wide)
3 inch	4.75 mm	22.2 mm	0.380 mm	1.58 mm	3.17 mm
(75 mm)	0.187 in	0.874 in	0.015 in	0.062 in	0.125 in
4 inch	4.75 mm	32.5 mm	0.625 mm	1.54 mm	3.21 mm
(100 mm)	0.187 in	1.280 in	0.025 in	0.061 in	0.126 in
5 inch	4.75 mm	42.5 mm	0.625 mm	1.52 mm	3.23 mm
(125 mm)	0.187 in	1.673 in	0.025 in	0.060 in	0.127 in
6 inch	4.75 mm	57.5 mm	0.675 mm	1.43 mm	3.33 mm
(150 mm)	0.187 in	2.264 in	0.027 in	0.056 in	0.131 in
8 inch	6.35 mm	59.3 mm	0.725 mm	2.19 mm	4.16 mm
(200 mm)	0.250 in	2.335 in	0.029 in	0.086 in	0.164 in

DIMENSIONS (Unit: mm in)



Refer to p.1552~ for general precautions.

- From the above, it is seen that, since the pitch of the cross-condition wafer reduces, the pitch resolution required for high reflectivity wafers becomes more stringent than the specified resolution of 3 mm 0.118 in. Hence, the sensing signal from two wafers may not be resolved and may become a continuous signal.
 Further, the sensing signal may also change due to the sensing conditions (sensing distance or sensing angle). For the above reasons, in case of wafers which have been cross-inserted, since the small cross-pitch side is similar to overlapping wafers, the sensing signal of two wafers may become a continuous signal or may get resolved.
- If the orientation flat happens to get in the position of sensing, sensing is not possible in one of the two sensing positions. Therefore, if the wafer is cross-inserted, a resolved signal may not be output, and in this case, the information on the wafer position calculated from the sensing signal will be erroneous.

The CAD data can be downloaded from our website.

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